



STB80NE03L-06 STB80NE03L-06-1

N-CHANNEL 30V - 0.005Ω - 80A D²PAK / I²PAK

STripFET™ POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB80NE03L-06	30 V	< 0.006 Ω	80 A
STB80NE03L-06-1	30 V	< 0.006 Ω	80 A

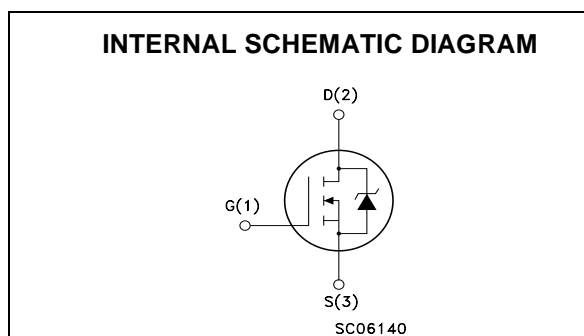
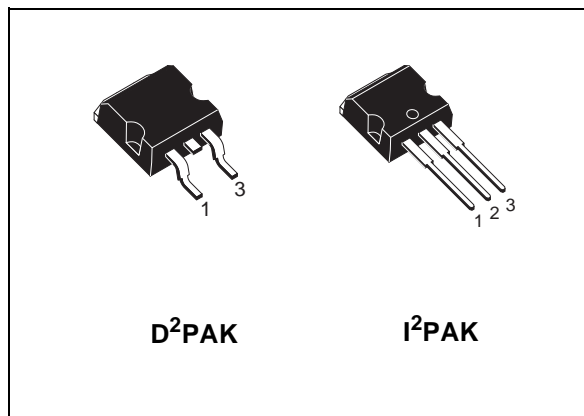
- TYPICAL R_{DS(on)} = 0.005 Ω
- EXCEPTIONAL dv/dt CAPABILITY
- LOW GATE CHARGE 100°C
- 100% AVALANCHE TESTED

DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	80	A
I _D	Drain Current (continuous) at T _C = 100°C	60	A
I _{DM} (●)	Drain Current (pulsed)	320	A
P _{TOT}	Total Dissipation at T _C = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	7	V/ns
T _{stg}	Storage Temperature	- 55 to 175	°C
T _j	Max. Operating Junction Temperature		

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 804A, di/dt ≤ 300A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

STB80NE03L-06 / STB80NE03L-06-1**THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	80	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 15 V)	600	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1	1.7	2.5	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V, I _D = 40 A V _{GS} = 4.5 V, I _D = 40 A		0.005	0.006 0.008	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 40 A	30	50		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		6500		pF
C _{oss}	Output Capacitance			1500		pF
C _{rss}	Reverse Transfer Capacitance			500		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$		40	55	ns
t_r	Rise Time	$R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3)		260	350	ns
Q_g	Total Gate Charge	$V_{DD} = 24\text{ V}$, $I_D = 80\text{ A}$,		95	130	nC
Q_{gs}	Gate-Source Charge	$V_{GS} = 5\text{ V}$		30		nC
Q_{gd}	Gate-Drain Charge			44		nC

SWITCHING OFF

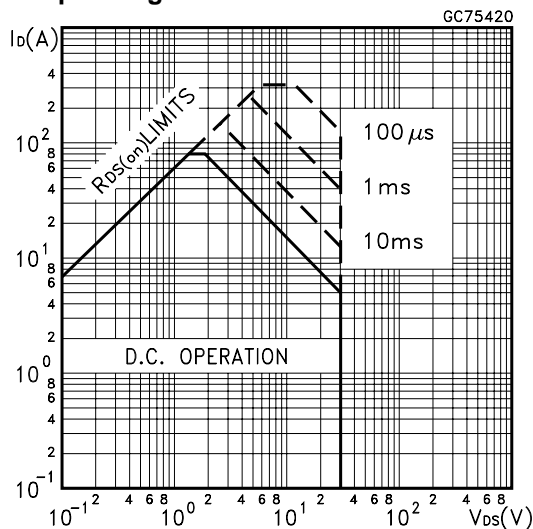
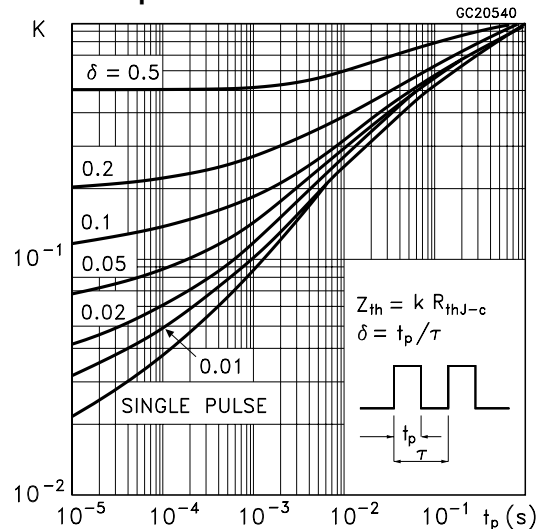
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{DD} = 24\text{ V}$, $I_D = 80\text{ A}$,		70	95	ns
t_f	Fall Time	$R_G = 4.7\Omega$, $V_{GS} = 5\text{ V}$		165	220	ns
t_c	Cross-over Time	(see test circuit, Figure 3)		250	340	ns

SOURCE DRAIN DIODE

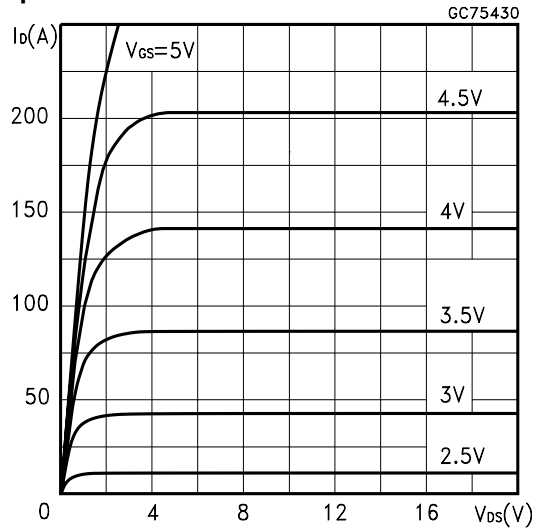
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				80	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				320	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 80\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,		75		ns
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 15\text{ V}$, $T_j = 150^\circ\text{C}$		0.14		nC
I_{RRM}	Reverse Recovery Current	(see test circuit, Figure 5)		4		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

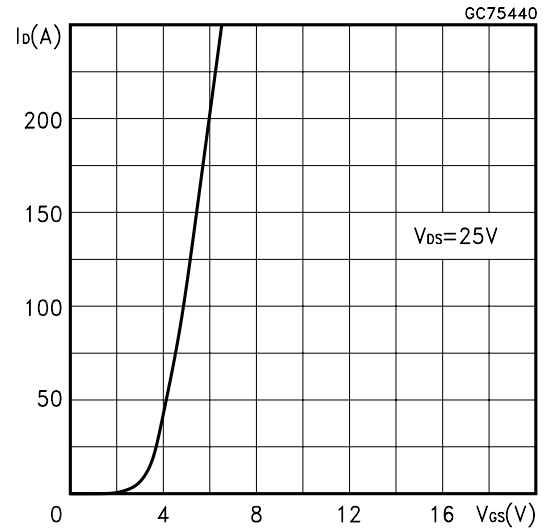
2. Pulse width limited by safe operating area.

Safe Operating Area**Thermal Impedence**

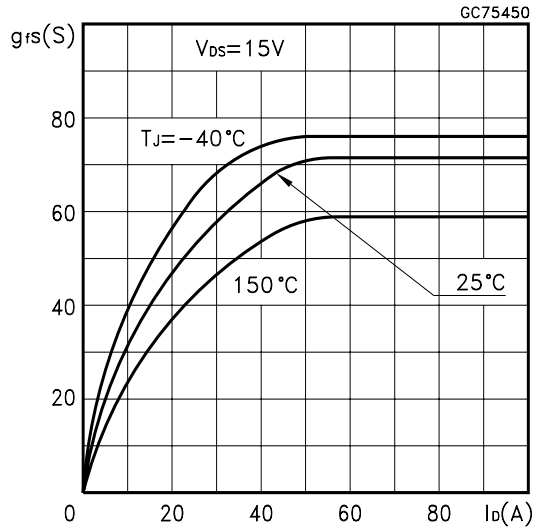
Output Characteristics



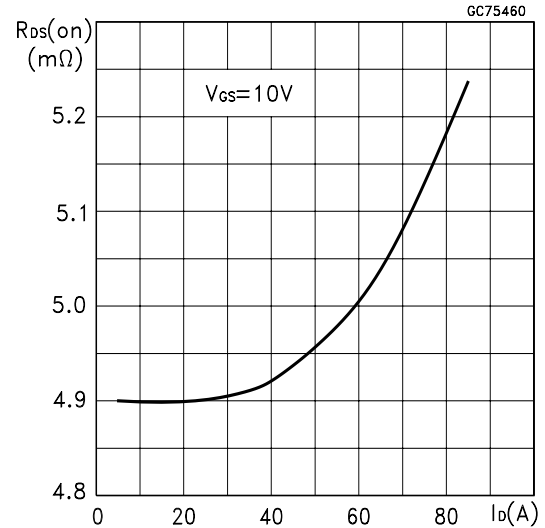
Transfer Characteristics



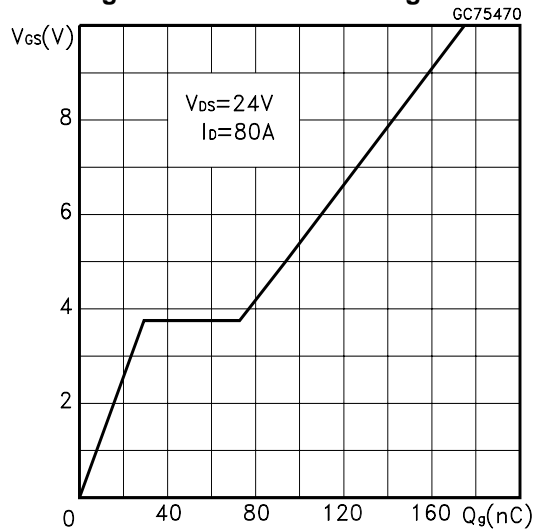
Transconductance



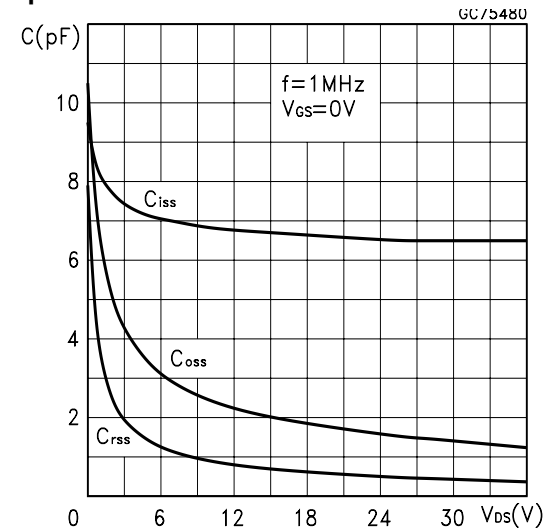
Static Drain-source On Resistance



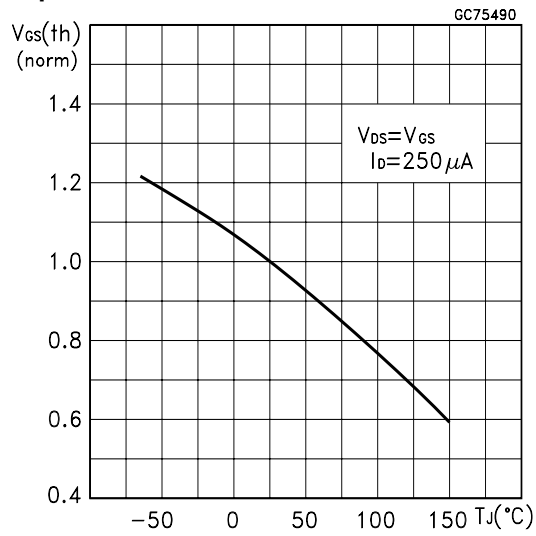
Gate Charge vs Gate-source Voltage



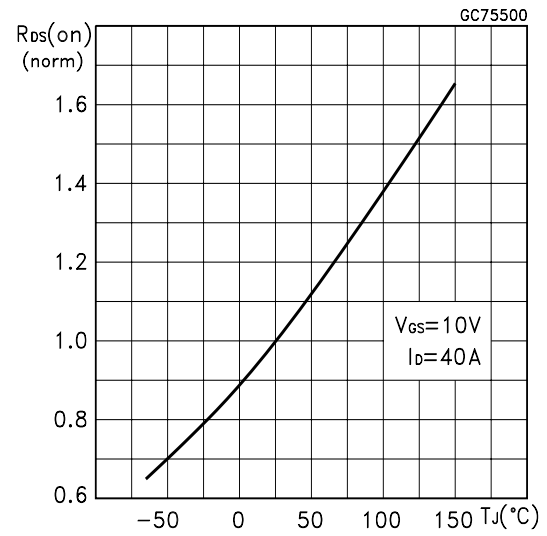
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

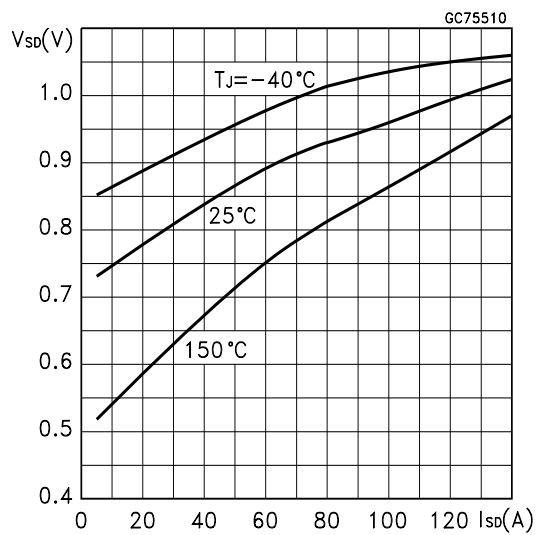


Fig. 1: Unclamped Inductive Load Test Circuit

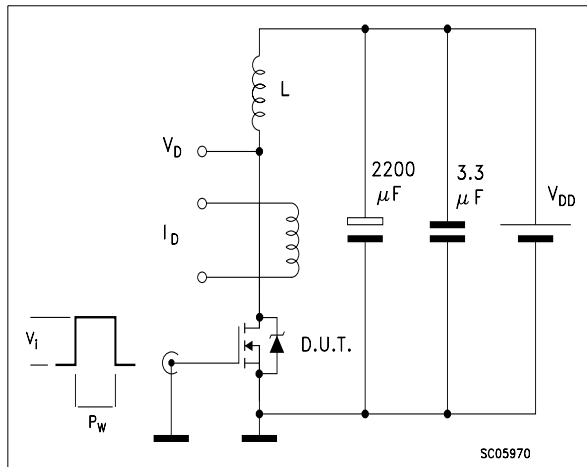


Fig. 2: Unclamped Inductive Waveform

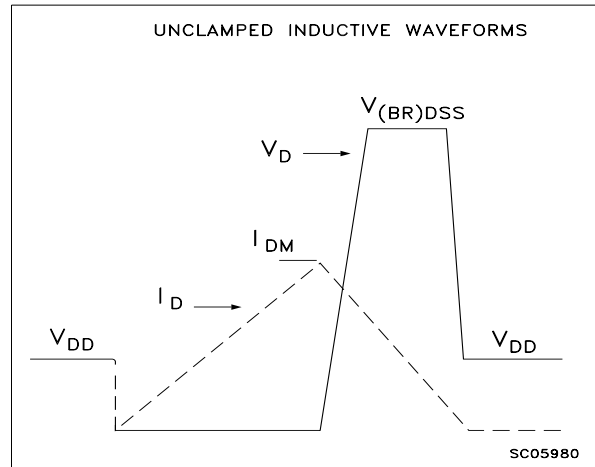


Fig. 3: Switching Times Test Circuit For Resistive Load

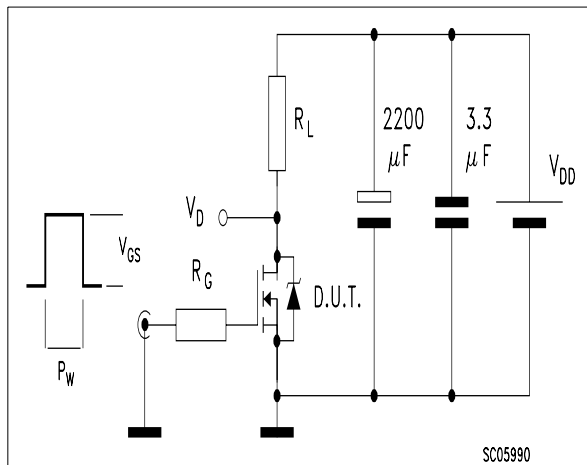


Fig. 4: Gate Charge test Circuit

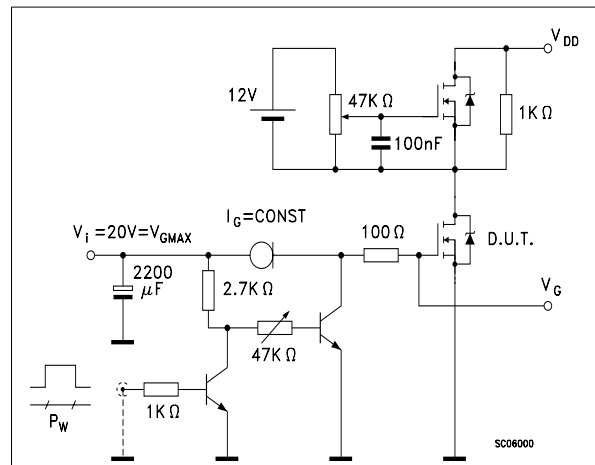
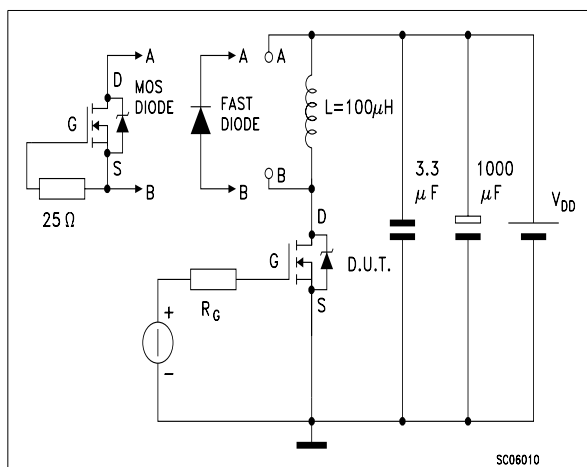
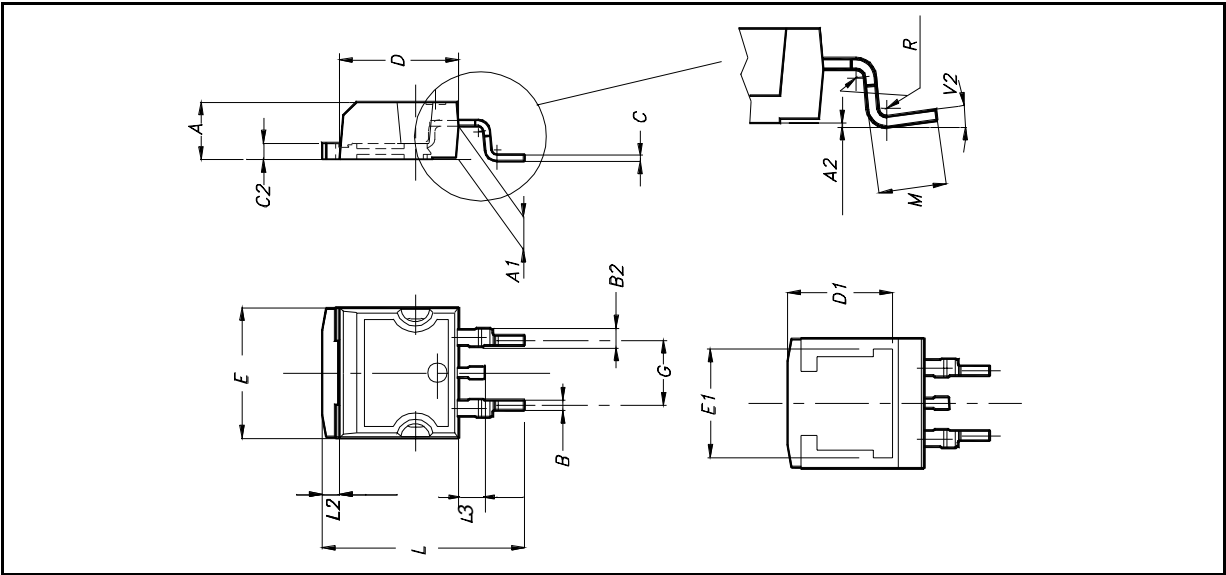


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



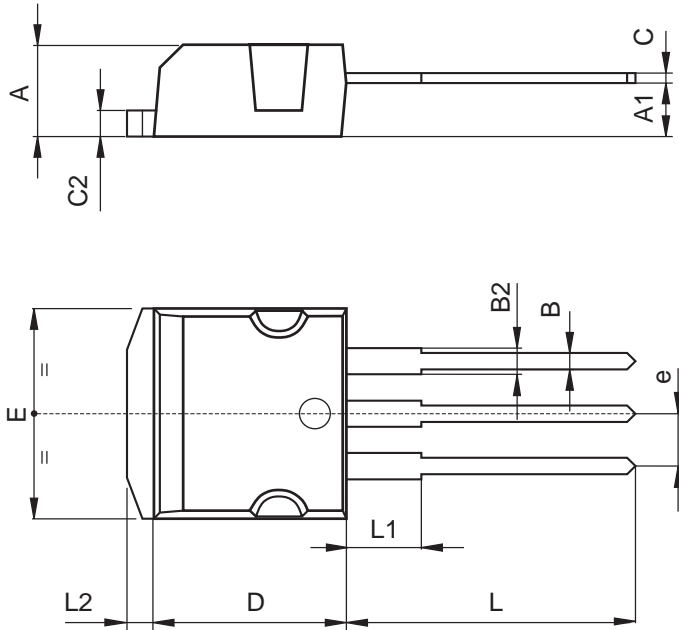
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055



P011P5/E

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

© <http://www.st.com>